

isc Silicon NPN Power Transistor

2SD1832

DESCRIPTION

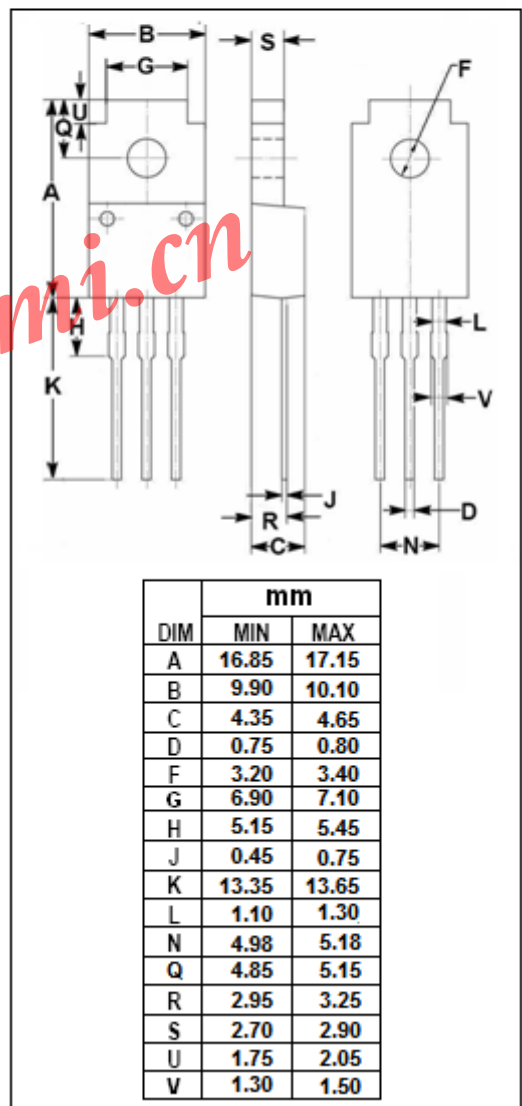
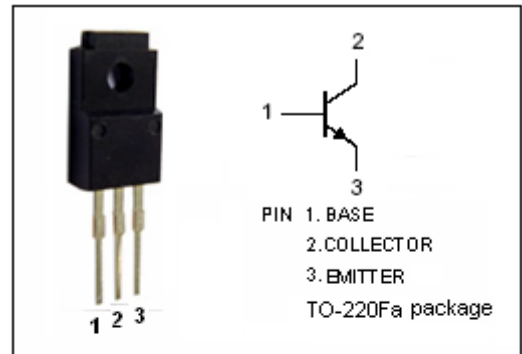
- High Collector Current:: $I_C = 5A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 1.0V(\text{Max.}) @ I_C = 3A$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Total Power Dissipation @ $T_C = 25^\circ C$	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 50 μ A; I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 50 μ A; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.3A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 0.3A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 5V	60		320	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		130		pF
f _T	Current-Gain Bandwidth Product	I _E = -0.5A; V _{CE} = 5V		8		MHz

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320